

IN THE CLAIMS:

1. (Currently amended) A semiconductor capacitor comprising:

a first conductive section having a first outer plate connected to a first inner plate, wherein the first outer plate and the first inner plate are substantially coplanar with one another; and

a second conductive section having a second outer plate connected to a second inner plate, wherein the second outer plate and the second inner plate are substantially coplanar with one another, and wherein the second inner plate is located within a first hole in the first outer plate and the first inner plate is located within a second hole in the second outer plate such that a first distance is present between the second inner plate and the first outer plate and a second distance is present between the first inner plate and the second outer plate.

2. (Currently amended) The semiconductor capacitor of claim 1, wherein the first conductive section and the second conductive section are substantially coplanar with one another ~~the semiconductor capacitor is a complementary metal oxide semiconductor capacitor.~~

3. (Original) The semiconductor capacitor of claim 1, wherein the first outer plate and the second outer plate have a rectangular shape.

4. (Original) The semiconductor capacitor of claim 1, wherein the first distance is equal to the second distance.

5. (Original) The semiconductor capacitor of claim 1, wherein the first distance is about 0.2 μm and the second distance is about 0.2 μm .

6. (Original) The semiconductor capacitor of claim 1, wherein the first section and the second section have a thickness of about 0.25 μm to about 0.45 μm .

7. (Original) The semiconductor capacitor of claim 1 further comprising:

a third conductive section having an third outer plate connected to a third inner plate; and

a fourth conductive section having a fourth outer plate connected to a fourth inner plate, wherein the fourth inner plate is located within a third hole in the third outer plate and the third inner plate is located within a fourth hole in the fourth outer plate such that a third distance is present between the fourth inner plate and the third outer plate and a fourth distance is present between the third inner plate and the fourth outer plate and wherein the third conductive section and the fourth conductive section are located below the first conductive section and the second conductive section.

8. (Currently amended) The semiconductor capacitor of claim 1, wherein the third outer plate is located below the first outer plate, fourth outer plate is located below the second outer plate, the third inner plate is located below the first inner plate, and the fourth inner plate is located below the second inner plate.

9. (Original) The semiconductor capacitor of claim 1, the first conductive section is connected to a third conductive section by a first set of via connections and wherein the second conductive section is connected to the fourth conductive section by a second set of via connections.

10. (Original) The semiconductor capacitor of claim 9, wherein first conductive section is spaced apart of the third section by about 0.2 μm and the second conductive section is spaced apart from the fourth conductive section by about 0.2 μm .

11. (Currently amended) The semiconductor capacitor of claim 1, wherein the first conductive section and the second conductive section are formed from a common metal layer.

12. (Currently amended) The semiconductor capacitor of claim 1, wherein the first outer plate is connected to the first inner plate by a first metal line and wherein the second

outer plate is connected to the second inner plate by a second metal line, and wherein the first metal line and the second metal line are formed from a common metal layer.

13-15. (Canceled)